

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI S50-28** is Designed for Class AB or C, Common Emitter Linear HF Communications Applications.

FEATURES INCLUDE:

- High Power Gain
- Emitter Ballasting

MAXIMUM RATINGS

I_C	9.0 A
V_{CB}	65 V
P_{DISS}	117 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	1.7 °C/W

PACKAGE STYLE .500" 4L FLG

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	.125/3,18	
C	.245/6,22	.255/6,48
D	.720/18,28	.730/18,54
E	.125/3,18	
F	.970/24,64	.980/24,89
G	.495/12,57	.505/12,83
H	.003/0,08	.007/0,18
I	.090/2,29	.110/2,79
J	.160/4,06	.175/4,45
K		.280/7,11
L		1.050/26,67

1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 200 mA	65			V
BV_{CEO}	I _C = 200 mA	35			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CBO}	V _{CB} = 30 V			2.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 500 mA	10		200	---
C_{ob}	V _{CB} = 30 V f = 1.0 MHz			150	pF
P_{out}	V _{CE} = 28 V P _{in} = 1.0 W fo = 30 MHz	50	60		W
P_G		17	18		dB
η_C			65		%